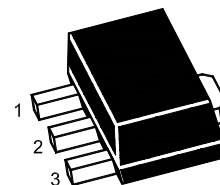


Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURE

- High voltage
- Large continuous collector current capability



SOT-89

1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

MARKING: 1013

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-1	A
P_C	Collector Power Dissipation	0.5	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	$^{\circ}\text{C/W}$

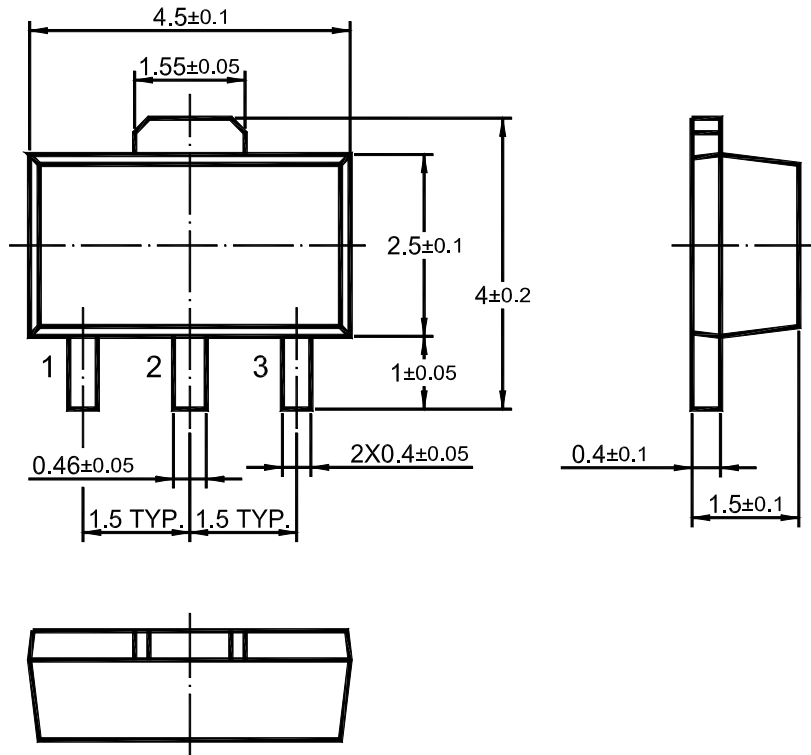
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-160		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}$, $I_C=0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB}=-150\text{V}$, $I_E=0$		-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6\text{V}$, $I_C=0$		-1	μA
DC current gain	h_{FE}	$V_{CE}=-5\text{V}$, $I_C=-200\text{mA}$	60	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$		-1.5	V
Base-emitter voltage	V_{BE}	$I_C=-5\text{mA}$, $V_{CE}=-5\text{V}$		-0.75	V
Transition frequency	f_T	$V_{CE}=-5\text{V}$, $I_C=-200\text{mA}$	15		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	60-120	100-200	160-320

SOT-89 PACKAGE OUTLINE



Dimensions in mm